

**SiC SCHOTTKY DIODE TYPE 2×100A**

**Features**

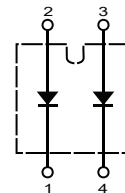
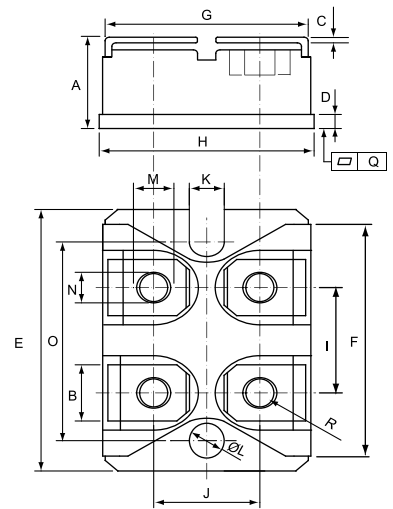
- High surge current capable
- Zero reverse recovery
- Zero forward recovery
- Isolation type package
- Temperature independent switching behavior
- $V_{DC}$  1200 V
- $I_F$  ( $T_c < 135^\circ C$ ) 2×100 A

**Benefits**

- Unipolar rectifier
- Higher efficiency
- Smaller heat sink

**Applications**

- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- induction heating



parallel

**Maximum Ratings**

Operating Junction Temperature :  $-55^\circ C$  to  $+175^\circ C$

Storage Temperature :  $-55^\circ C$  to  $+175^\circ C$

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSRI2×100-120P3B	1200V	1200V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current (per diode)	$I_F$	$T_c = 135^\circ C$	100	A
Surge non-repetitive forward current sine halfwave (per diode)	$I_{FSM}$	$T_c = 25^\circ C, t_p = 8.3 \text{ ms}$	800	
		$T_c = 150^\circ C, t_p = 8.3 \text{ ms}$	500	
Non-repetitive peak forward current (per diode)	$I_{F,max}$	$T_c = 25^\circ C, t_p = 10 \mu s$	3200	
		$T_c = 150^\circ C, t_p = 10 \mu s$	2000	
Repetitive peak reverse voltage	$V_{RRM}$	$T_j = 25^\circ C$	1200	V
Isolation voltage (between All Terminals and Baseplate)	$V_{iso}$	50/60 Hz, $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$	2500	V
Mounting torque	$M_d$	To heatsink	1.3	Nm
		To terminal	1.1	

	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			

**Electrical Characteristics**, at  $T_J=25\text{ }^\circ\text{C}$ , unless otherwise specified. (per diode)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	$V_{DC}$		1,200	-	-	V
Diode forward voltage	$V_F$	$I_F=100\text{A}$ , $T_J=25\text{ }^\circ\text{C}$	-	1.5	1.7	V
		$I_F=100\text{A}$ , $T_J=175\text{ }^\circ\text{C}$	-	2.2	2.7	
Reverse current	$I_R$	$V_R=1,200\text{V}$ , $T_J=25\text{ }^\circ\text{C}$	-	60	100	$\mu\text{A}$
		$V_R=1,200\text{V}$ , $T_J=175\text{ }^\circ\text{C}$	-	100	500	

**AC Characteristics** (per diode)

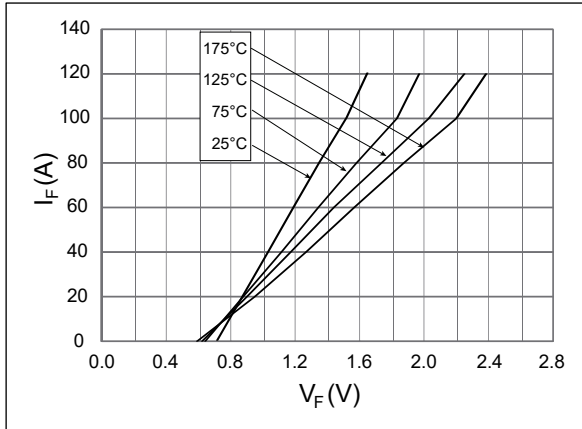
Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	$Q_{rr}$	$di/dt=1100\text{A}/\mu\text{s}$ $I_F=100\text{A}$ , $V_R=800\text{V}$	-	410	-	nC
Total capacitance	C	$V_R=0\text{V}$ , $f=1\text{ MHz}$ $T_J=25\text{ }^\circ\text{C}$	-	5,790	-	pF
		$V_R=400\text{V}$ , $f=1\text{ MHz}$ $T_J=25\text{ }^\circ\text{C}$	-	460	-	
		$V_R=800\text{V}$ , $f=1\text{ MHz}$ $T_J=25\text{ }^\circ\text{C}$	-	327	-	

**Thermal Characteristics** (per diode)

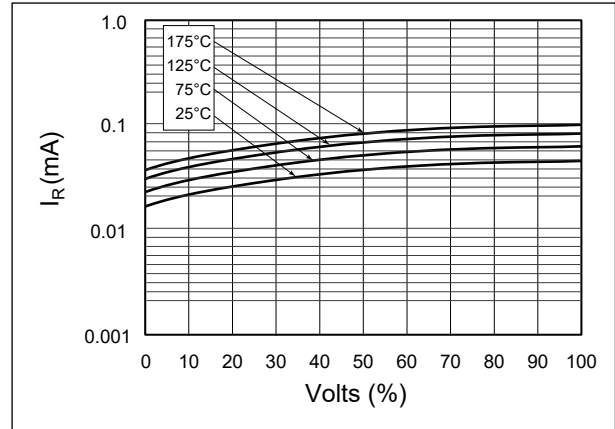
Static Characteristics	Symbol	Values	Unit
		typ.	
Thermal resistance from junction to case	$R_{\theta JC}$	0.14	$^\circ\text{C}/\text{W}$

Typical Performance

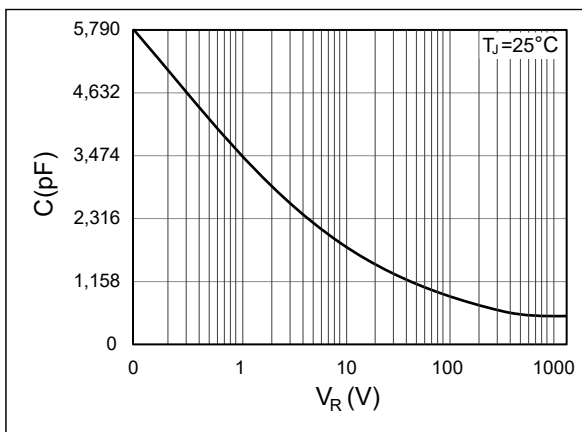
Forward Characteristics (parameterized on  $T_j$ )



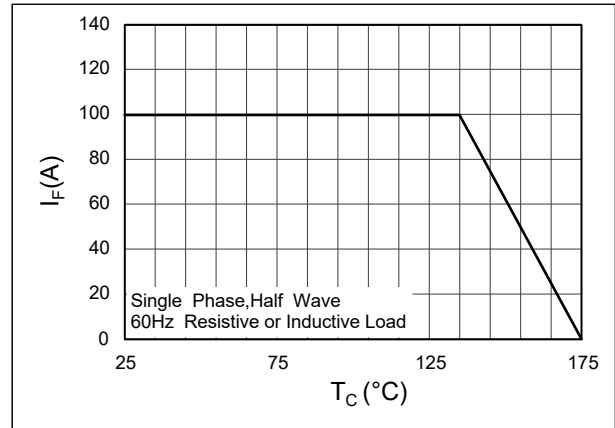
Reverse Characteristics (parameterized on  $T_j$ )



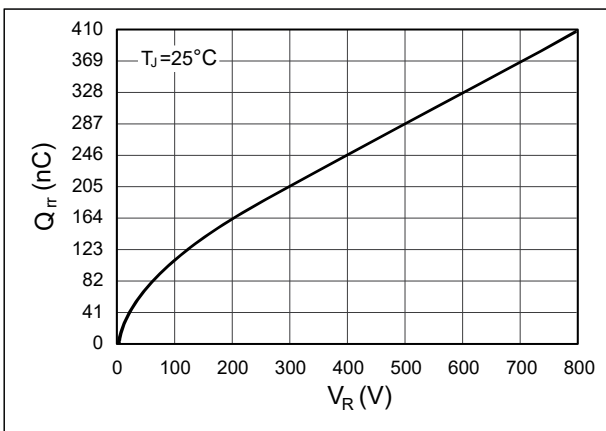
Capacitance



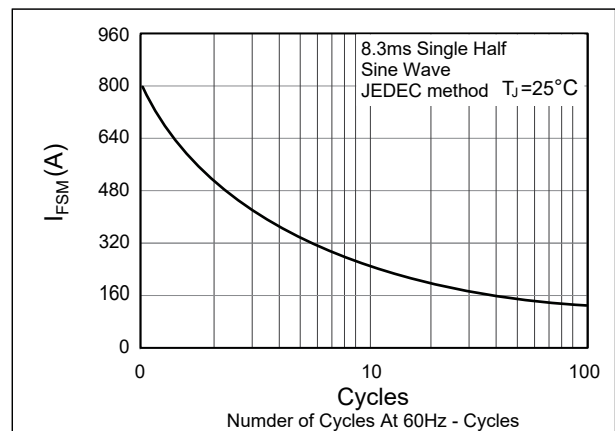
Current Derating



Recovery Charge



Forward Surge Current



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